

2N**5533** (SILICON)

RADIATION RESISTANT SILICON NPN POWER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS

VCBO V	VCEO V	IC A	IB A	PT W	QJ-C °C/W	QJ-A °C/W	CASE TYPE
90	75	10	2	35	2.5	45	TO-61*

SYMBOL	TEST CONDITIONS				UNIT
		MIN.	TYP.	MAX.	
V _{CBO}	I _{CBO} = 1 mA	90	100	—	V
V _{CEO}	I _{CEO} = 50 mA	75	—	—	V
V _{EBO}	I _{EBO} = 1 mA	3	5	—	V
I _{CBO}	V _{CBO} = 30 V	—	—	0.1	mA
h _{FE} †	I _C = 0.5 A, V _{CE} = 5 V	25	—	—	—
h _{FE} †	I _C = 3 A, V _{CE} = 5 V	30	—	150	—
h _{FE} †	I _C = 5 A, V _{CE} = 5 V	20	—	—	—
V _{CE} (s)	I _C = 3 A, I _B = 0.5 A	—	0.5	1	V
V _{BE} (s)	I _C = 3 A, I _B = 0.5 A	—	—	1.5	V

† Pulse width = 300 μs, duty cycle = 2%

TO-61 PACKAGE

